

Product Overview

NSS40600CF8: Bipolar Transistor, Low $V_{CE(sat)}$, PNP, 6.0 A, 40 V

For complete documentation, see the data sheet.

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Current, Low $V_{CE(sat)}$, ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AECQ101 Qualified and PPAP Capable

Benefits

- Improved Circuit Efficiency, Decreased Battery Charge Time, Reduce component count, High Frequency Switching, Smaller Portable Product, No distortion

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extension & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

End Products

- Portable products

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}^{(Ic)}$ Max (V)	I_c Cont. (A)	$V_{CEO}^{(Ic)}$ Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(0)}$ (V)	$h_{FE}^{(Ic)}$ Min	$h_{FE}^{(Ic)}$ Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
NSS40600CF8T1G	0.2133	Pb-free Halide free	Active	PNP	Low $V_{CE(sat)}$	0.075	6	40	40	7	0.9	0.9	250	-	100	2.75	Chip FET-8
SNSS40600CF8T1G	0.2347	AEC Qualified PPAP Capable Pb-free Halide free	Active	PNP	Low $V_{CE(sat)}$	0.075	6	40	40	7	0.9	0.9	250	-	100	2.75	Chip FET-8

For more information please contact your local sales support at www.onsemi.com.

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